Supporting information for: Boron-Doped Graphene Topological Defects: Unveiling High Sensitivity to NO Gas Molecules for Gas Sensing Applications

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Table S1: Dopant substitutional energies of B impurity in graphene with line defect unit cell. B-doped adsorption sites according to Figure 1. The most stable site is set as zero.

B-doped Sites	1	2	3	5
$\Delta E \ (eV)$	0.10	0.00	0.71	0.14



Figure S1: The calculated projected density of states for B-doped defective graphene. B atom occupies the most stable site (2), where C_1 , C_3 , and C_5 atoms are the first neighbors of it. The total dos normalized by the total number of atoms is also shown.



Figure S2: Zero bias transmission as a function of the energy for the B-doped line defect in graphene device with and without gas molecule a) CO and CO_2 gas; b) NO and NH_3 gas.